

1. General description

Ultrafast power diode in a SOD142 (2-lead TO247) plastic package.

2. Features and benefits

- Fast switching
- Low forward voltage drop
- Low thermal resistance
- Soft recovery characteristic
- Reduces switching losses in associated MOSFET or IGBT
- Planar passivated for voltage ruggedness and reliability

3. Applications

- Switched-Mode Power Supplies
- Power factor correction diode
- Uninterrupted Power Supply
- Motor drive and SMPS freewheeling diode

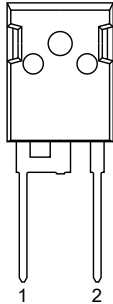

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_R	reverse voltage	DC	-	-	1200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 98$ °C; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	-	16	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; Fig. 4	-	-	150	A
		$t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse	-	-	165	A
Static characteristics						
V_F	forward voltage	$I_F = 16$ A; $T_j = 25$ °C; Fig. 6	-	2.3	3	V
		$I_F = 32$ A; $T_j = 25$ °C; Fig. 6	-	2.8	3.9	V
		$I_F = 16$ A; $T_j = 125$ °C; Fig. 6	-	1.8	2.7	V
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1$ A; $V_R = 30$ V; $di_F/dt = 200$ A/ μ s; $T_j = 25$ °C; Fig. 7	-	40	-	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 <p style="text-align: center;">TO-247 (SOD142)</p>	
2	A	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

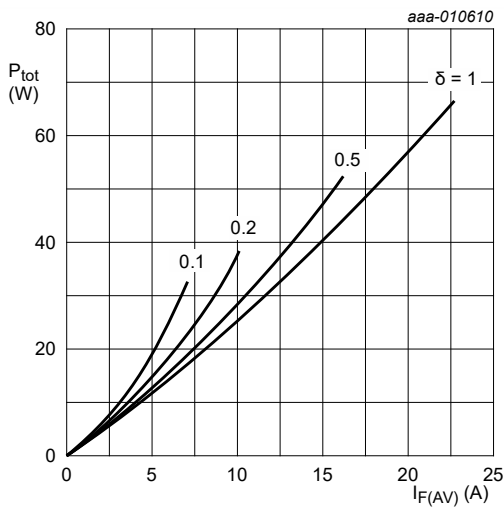
Type number	Package		
	Name	Description	Version
BYR16W-1200	TO-247	Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247	SOD142

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

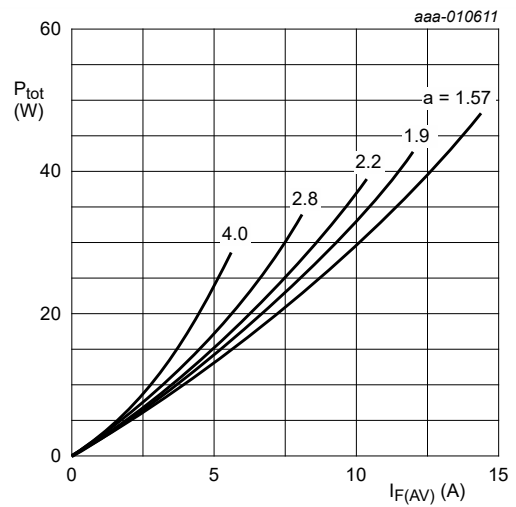
Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	1200	V
V_{RWM}	crest working reverse voltage		-	1200	V
V_R	reverse voltage	DC	-	1200	V
$I_{F(AV)}$	average forward current	$\delta = 0.5$; $T_{mb} \leq 98\text{ }^\circ\text{C}$; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3	-	16	A
I_{FRM}	repetitive peak forward current	$\delta = 0.5$; $t_p = 25\text{ }\mu\text{s}$; $T_{mb} \leq 98\text{ }^\circ\text{C}$; square-wave pulse	-	32	A
I_{FSM}	non-repetitive peak forward current	$t_p = 10\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; sine-wave pulse; Fig. 4	-	150	A
		$t_p = 8.3\text{ ms}$; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$; sine-wave pulse	-	165	A
T_{stg}	storage temperature		-55	150	$^\circ\text{C}$
T_j	junction temperature		-	150	$^\circ\text{C}$



$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

$$V_o = 0.79\text{ V}; R_s = 0.008\text{ }\Omega$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values



$$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$$

$$V_o = 2.210\text{ V}; R_s = 0.032\text{ }\Omega$$

Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

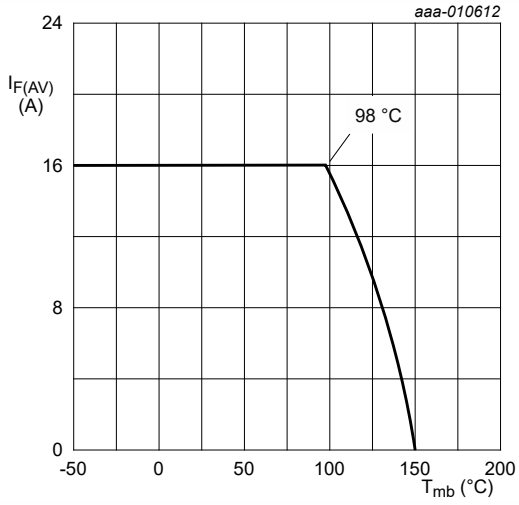


Fig. 3. Forward current as a function of mounting base temperature; maximum values

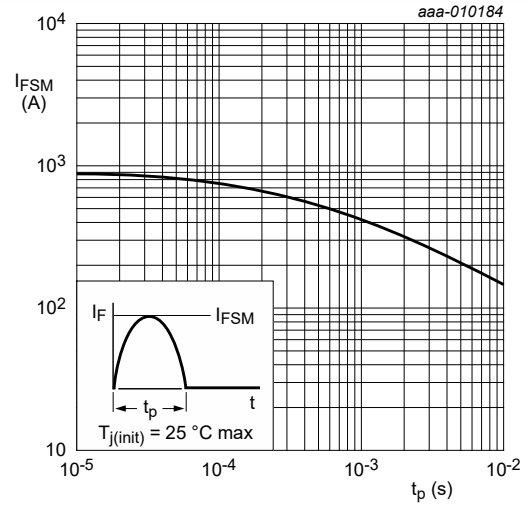


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	with heatsink compound; Fig. 5	-	-	1	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W

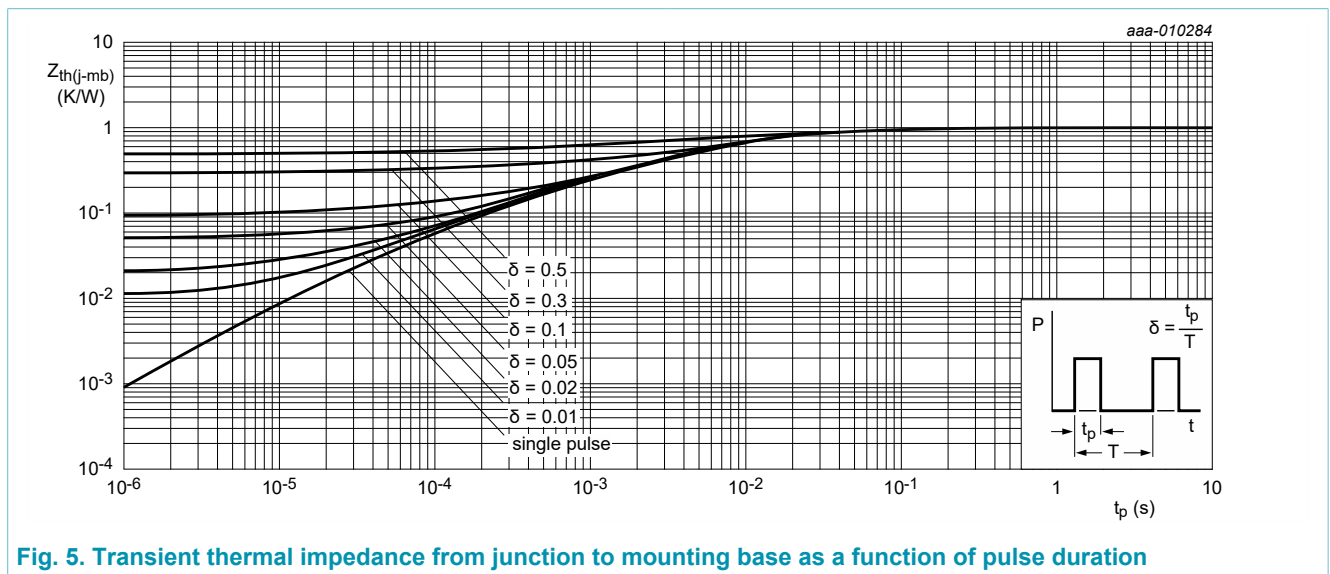
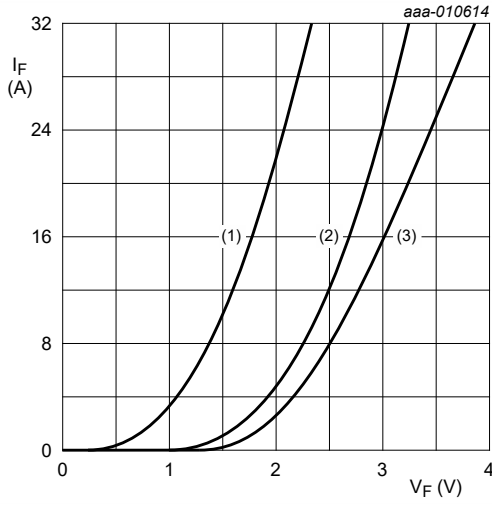


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	$I_F = 16\text{ A}; T_j = 25\text{ °C};$ Fig. 6	-	2.3	3	V
		$I_F = 32\text{ A}; T_j = 25\text{ °C};$ Fig. 6	-	2.8	3.9	V
		$I_F = 16\text{ A}; T_j = 125\text{ °C};$ Fig. 6	-	1.8	2.7	V
I_R	reverse current	$V_R = 1200\text{ V}; T_j = 25\text{ °C}$	-	3	100	μA
		$V_R = 1200\text{ V}; T_j = 125\text{ °C}$	-	0.2	2	mA
Dynamic characteristics						
t_{rr}	reverse recovery time	$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	40	-	ns
		$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	90	-	ns
		$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	150	-	ns
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	105	-	ns
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	200	-	ns
		$I_F = 1\text{ A}; V_R = 30\text{ V}; dI_F/dt = 100\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	50	-	ns
I_{RM}	peak reverse recovery current	$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	11.2	-	A
		$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	16	-	A
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	11.2	-	A
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	16.2	-	A
Q_r	recovered charge	$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	520	-	nC
		$I_F = 16\text{ A}; V_R = 200\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	1200	-	nC
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 25\text{ °C};$ Fig. 7	-	605	-	nC
		$I_F = 16\text{ A}; V_R = 400\text{ V}; dI_F/dt = 200\text{ A}/\mu\text{s}; T_j = 125\text{ °C};$ Fig. 7	-	1600	-	nC



$V_o = 2.210 \text{ V}; R_s = 0.032 \Omega$
 (1) $T_j = 150 \text{ }^\circ\text{C}$; typical values
 (2) $T_j = 150 \text{ }^\circ\text{C}$; maximum values
 (3) $T_j = 25 \text{ }^\circ\text{C}$; maximum values

Fig. 6. Forward current as a function of forward voltage

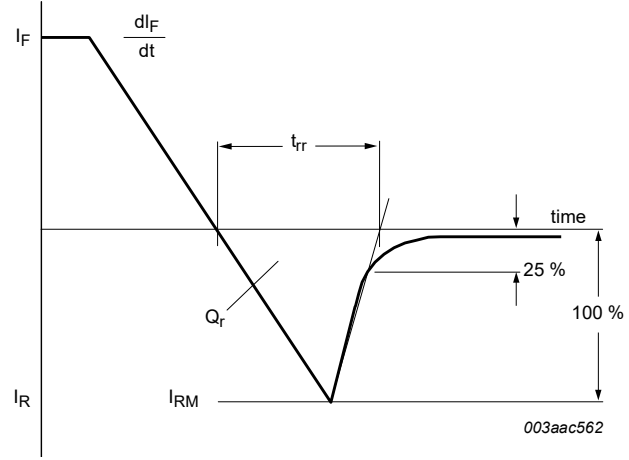
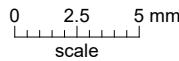
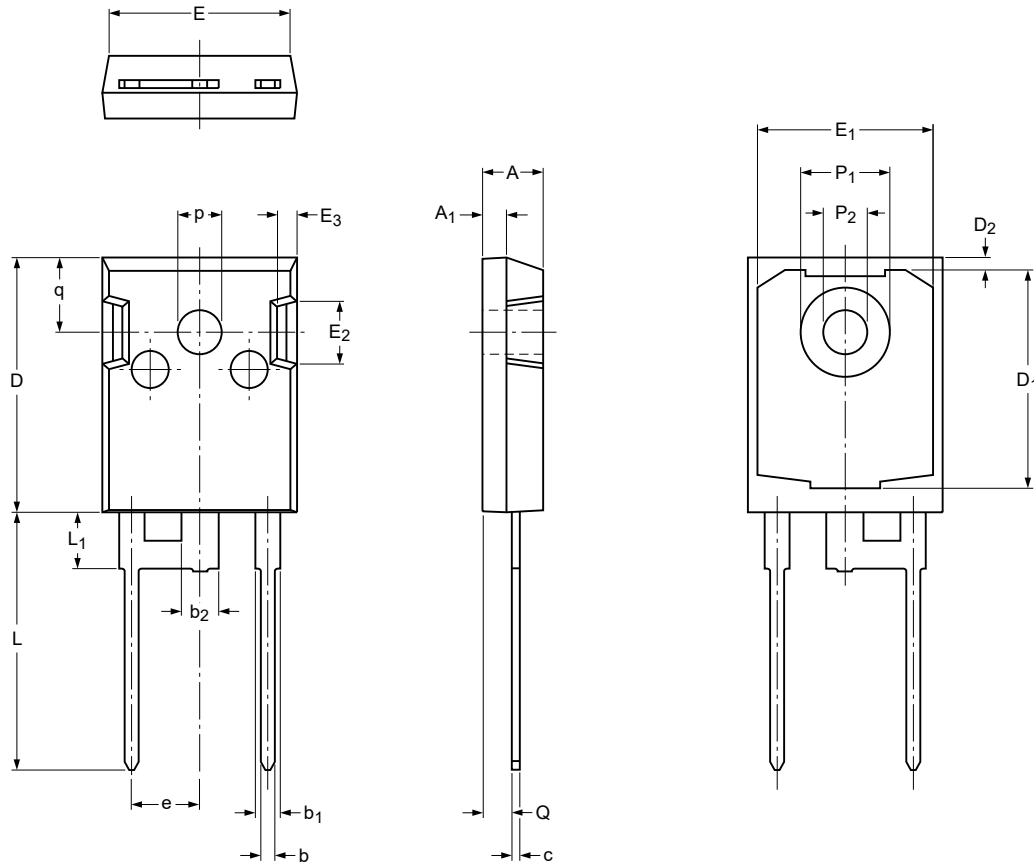


Fig. 7. Reverse recovery definitions; ramp recovery

10. Package outline

Plastic Single-ended through-hole package; Heatsink mounted; 1 mounting hole; 2-lead TO-247 SOD142



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b	b ₁	b ₂	c	D	D ₁	D ₂	e	E	E ₁	E ₂	E ₃	L	L ₁	p	p ₁	p ₂	q	Q	
mm	max	5.2	2.1	1.4	2.2	3.2	0.7	20.6	17.68	1.2	15.75	14.22	5.2	1.8	20.9	4.75	3.7	7.3	3.6	6.18	2.6	
	nom									5.45												
	min	4.7	1.9	1.0	1.8	2.8	0.5	20.3	17.28	0.8	15.45	13.82	4.8	1.4	20.4	4.25	3.5	7.1	3.4	5.78	2.2	

sod142_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOD142	TO247				-12-11-13- 12-11-27

Fig. 8. Package outline TO-247 (SOD142)

11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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